

Photocouplers Infrared LED & Photo IC

TLP700H

1. Applications

- · Industrial Inverters
- · Air Conditioner Inverters
- · MOSFET Gate Drivers
- · IGBT Gate Drivers
- · Induction Cooktop and Home Appliances

2. General

The TLP700H is a photocoupler in a 6-pin SDIP package that consists of an infrared LED optically coupled to an integrated high-gain, high-speed photodetector IC chip. It provides guaranteed performance and specifications at temperatures up to $125\,^{\circ}$ C.

The TLP700H is physically smaller than the one in an 8-pin DIP package and compliant with international safety standards for reinforced insulation. It thus provides a smaller footprint solution for applications that require safety standard certification. An internal noise shield provides a guaranteed commonmode transient immunity of $\pm 20 \text{ kV/}\mu s$. It is ideal for IGBT and power MOSFET gate drive.

3. Features

- (1) Buffer logic type (totem pole output)
- (2) Output peak current: ±2.5 A (max)
- (3) Operating temperature: -40 to 125 °C
- (4) Supply current: 3 mA (max)
- (5) Supply voltage: 15 to 30 V
- (6) Threshold input current: 5 mA (max)
- (7) Propagation delay time: 500 ns (max)
- (8) Common-mode transient immunity: ±20 kV/μs (min)
- (9) Isolation voltage: 5000 Vrms (min)
- (10) Safety standards

UL-recognized: UL 1577, File No.E67349

cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349

VDE-approved: EN 60747-5-5, EN 62368-1 (Note 1)

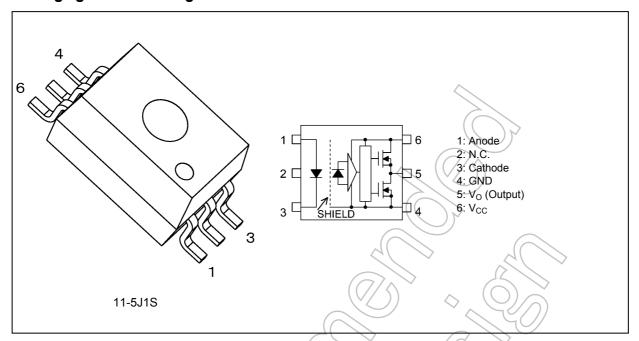
Note 1: When a VDE approved type is needed, please designate the Option (D4).



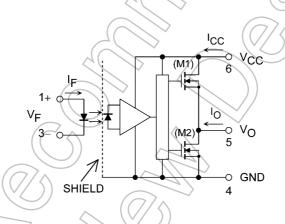
Start of commercial production



4. Packaging and Pin Configuration



5. Internal Circuit (Note)



Note: A 0.1- μF bypass capacitor must be connected between pin 6 and pin 4.

6. Principle of Operation

6.1. Truth Table

Input	LED	M1	M2	Output
H	ON	ON	OFF	Н
	OFF	OFF	ON	L

6.2. Mechanical Parameters

Characteristics	7.62 mm Pitch TLP700H	10.16 mm Pitch TLP700HF	Unit
Creepage distances	7.0 (min)	8.0 (min)	mm
Clearance distances	7.0 (min)	8.0 (min)	
Internal isolation thickness	0.4 (min)	0.4 (min)	



7. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteristics		Symbol	Note	Rating	Unit
LED	Input forward current		I _F		20	mA
	Input forward current derating	(T _a ≥ 116 °C)	$\Delta I_F/\Delta T_a$		-0.6	mA/°C
	Peak transient input forward current		I _{FPT}	(Note 1)	1	А
	Peak transient input forward current derating	(T _a ≥ 110 °C)	$\Delta I_{FPT}/\Delta T_a$	(-25	mA/°C
	Input reverse voltage		V _R		5	V
	Input power dissipation		P _D		40	mW
	Input power dissipation derating	(T _a ≥ 110 °C)	$\Delta P_D/\Delta T_a$		-1.0	mW/°C
Detector	Peak high-level output current	(T _a = -40 to 125 °C)	I _{OPH}	(Note 2)	-2.5	Α
	Peak low-level output current	(T _a = -40 to 125 °C)	lopu	(Note 2)	+2.5	1
	Output voltage		Vo	_	35	V
	Supply voltage		V _{QC}		35]
	Output power dissipation		(/ P ₀)	\Diamond	160	mW
	Output power dissipation derating	(T _a ≥ 110 °C)	$\Delta P_0/\Delta T_a$		4.0	mW/°C
Common	Operating temperature	4	T _{opr}		-40 to 125	°C
	Storage temperature		T _{stg}		-55 to 150	
	Lead soldering temperature	(10(s)	T _{sol}	(Note 3)	260	
	Isolation voltage	AC, 60 s, R.H. ≤ 60 %	BVs	(Note 4)	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width (PW) \leq 1 μ s, 300 pps

Note 2: Exponential waveform. Pulse width $\leq 0.3~\mu s$, f $\leq 15~kHz$

Note $3: \ge 2$ mm below seating plane.

Note 4: This device is considered as a two-terminal device: Pins 1, 2 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.

8. Recommended Operating Conditions (Note)

Characteristics	Symbol	Note	Min	Тур.	Max	Unit
Input on-state current	I _{F(ON)}	(Note 1)	6.5	_	10	mA
Input off-state voltage	$V_{F(OFF)}$		0	_	0.8	٧
Supply voltage	V _{CC}	(Note 2)	15	_	30	
Peak high-level output current	I _{OPH}		_	_	-2.0	Α
Peak low-level output current	I _{OPL}		_	_	+2.0	
Operating frequency	f	(Note 3)	_	_	50	kHz

Note: The recommended operating conditions are given as a design guide necessary to obtain the intended performance of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this datasheet should also be considered.

Note: A ceramic capacitor $(0.1 \, \mu F)$ should be connected between pin 6 and pin 4 to stabilize the operation of a high-gain linear amplifier. Otherwise, this photocoupler may not switch properly. The bypass capacitor should be placed within 1 cm of each pin.

Note 1: The rise and fall times of the input on-current should be less than 0.5 μs .

Note 2: Denotes the operating range, not the recommended operating condition.

Note 3: Exponential waveform. $I_{OPH} \ge -2.0 \text{ A} \ (\le 0.3 \ \mu\text{s}), \ I_{OPL} \le 2.0 \text{ A} \ (\le 0.3 \ \mu\text{s}), \ T_a = 125 \ ^{\circ}\text{C}$



Electrical Characteristics (Note) (Unless otherwise specified, T_a = -40 to 125 °C)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input forward voltage	V _F			I _F = 10 mA, T _a = 25 °C		1.55	1.7	V
Input forward voltage temperature coefficient	$\Delta V_F/\Delta T_a$			I _F = 10 mA		-2.0	l	mV/°C
Input reverse current	I _R			V _R = 5 V, T _a = 25 °C			10	μА
Input capacitance	Ct			V = 0 V, f = 1 MHz, T _a = 25 °C) 60		pF
Peak high-level output current	I _{OPH}	(Note 1)	Fig. 12.1.1	I _F = 5 mA, V _{CC} = 15 V, V ₆₋₅ = -3.5 V		-1.6	-1.0	Α
				$I_F = 5 \text{ mA}, V_{CC} = 15 \text{ V}, V_{6-5} = -7 \text{ V}$		_	-2.0	
Peak low-level output current	I _{OPL}	(Note 1)	Fig. 12.1.2	I _F = 0 mA, V _{CC} = 15 V, V ₅₋₄ = 2.5 V	1.0	1.6	ı	
				$I_F = 0 \text{ mA}, V_{CC} = 15 \text{ V}, V_{5-4} = 7 \text{ V}$	2.0	<u>/</u>	//	
High-level output voltage	V _{OH}		Fig. 12.1.3	$I_F = 5 \text{ mA}, R_L = 200 \Omega,$ $V_{CC1} = +15 \text{ V}, V_{EE1} = -15 \text{ V}$	11.0	13.7	<u> </u>	٧
Low-level output voltage	V _{OL}		Fig. 12.1.4	$V_F = 0.8 \text{ V}, R_L = 200 \Omega,$ $V_{CC1} = +15 \text{ V}, V_{EE1} = -15 \text{ V}$		-14.9	-12.5	
High-level supply current	Іссн		Fig. 12.1.5	$I_F = 10 \text{ mA}, V_{CC} = 30 \text{ V},$ $V_O = \text{Open}$	(A)	1.5	3.0	mA
Low-level supply current	I _{CCL}		Fig. 12.1.6	$I_F = 0 \text{ mA}, V_{CC} = 30 \text{ V}, V_Q = \text{Open}$		1.5	3.0	
Threshold input current (L/H)	I _{FLH}			$V_{CC} = 15 \text{ V}, V_{O} > 1 \text{ V}$	/ —	1.4	5	
Threshold input voltage (H/L)	V _{FHL}			$V_{CC} = 15 \text{ V, } V_{O} < 1 \text{ V}$	0.8	_	_	V
Supply voltage	V _{CC}			-	15	_	30	
UVLO threshold voltage	V _{UVLO+}))	I _F = 5 mA, V _O > 2.5 V	11.0	12.5	13.5	
	V _{UVLO-}			$I_F = 5 \text{ mA}, V_O < 2.5 \text{ V}$	9.5	11.0	12.0	
UVLO hysteresis	UVLO _{HYS}	$((\))$		- \	_	1.5	_	

Note: All typical values are at $T_a = 25$ °C.

Note: This device is designed for low power consumption, making it more sensitive to ESD than its predecessors. Extra care should be taken in the design of circuitry and pc board implementation to avoid ESD problems.

Note 1: I_O application time $\leq 50 \mu s$; single pulse.

10. Isolation Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Conditions	Min	Тур.	Max	Unit
Total capacitance (input to output)	Cs	(Note 1)	V _S = 0 V, f = 1 MHz	_	1.0		pF
Isolation resistance	Rs	(Note 1)	V _S = 500 V, R.H. ≤ 60 %	10 ¹²	1014		Ω
Isolation voltage	BVs	(Note 1)	AC, 60 s	5000	_		Vrms

Note 1: This device is considered as a two-terminal device: Pins 1, 2 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.



11. Switching Characteristics (Note) (Unless otherwise specified, T_a = -40 to 125 °C)

Characteristics	Symbol	Note	Test Circuit	l lest Condition		Тур.	Max	Unit
Propagation delay time (L/H)	t _{pLH}	(Note 1)	Fig. 12.1.7	$I_F = 0 \rightarrow 5$ mA, $V_{CC} = 30$ V, $R_g = 20 \Omega$, $C_g = 10$ nF	50		500	ns
Propagation delay time (H/L)	t _{pHL}	(Note 1)		$I_F = 5 \rightarrow 0$ mA, $V_{CC} = 30$ V, $R_g = 20 \Omega$, $C_g = 10$ nF	50		500	
Rise time	t _r	(Note 1)		$I_F = 0 \rightarrow 5$ mA, $V_{CC} = 30$ V, $R_g = 20 \Omega$, $C_g = 10$ nF	(F	15		
Fall time	t _f	(Note 1)		$I_F = 5 \rightarrow 0$ mA, $V_{CC} = 30$ V, $R_g = 20 \Omega$, $C_g = 10$ nF	Z \$	8	_	
Pulse width distortion	t _{pHL} -t _{pLH}	(Note 1)		$I_F = 0 \longleftrightarrow 5 \text{ mA}, V_{CC} = 30 \text{ V},$ $R_g = 20 \Omega, C_g = 10 \text{ nF}$	<u></u>	_	250	
High-level common-mode transient immunity	CM _H	(Note 2)	Fig. 12.1.8	$V_{CM} = 1000 V_{p-p}, I_F = 5 \text{ mA}, V_{CC} = 30 \text{ V}, T_a = 25 ^{\circ}\text{C}, V_{O(min)} = 26 \text{ V}$	±20	±25	- //	kV/μs
Low-level common-mode transient immunity	CM _L	(Note 3)		$V_{CM} = 1000 V_{p.p}, I_F = 0 \text{ mA},$ $V_{CC} = 30 \text{ V}, T_a = 25 \text{ °C},$ $V_{O(max)} = 1 \text{ V}$	±20	±25	<u> </u>	

Note: All typical values are at $T_a = 25$ °C.

Note 1: Input signal (f = 25 kHz, duty = 50 %, $t_r = t_f = 5 \text{ ns or less}$).

C_L is less than 15 pF which includes probe and stray wiring capacitance.

Note 2: CM_H is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic high state ($V_O > 26 \text{ V}$).

Note 3: CM_L is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state ($V_O < 1 \text{ V}$).





12. Test Circuits and Characteristics Curves

12.1. Test Circuits

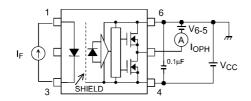


Fig. 12.1.1 I_{OPH} Test Circuit

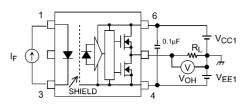


Fig. 12.1.3 V_{OH} Test Circuit

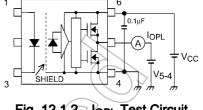


Fig. 12.1.2 JOPL Test Circuit

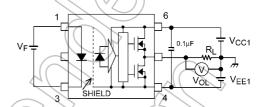


Fig. 12.1.4 Vol Test Circuit

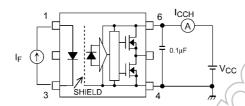


Fig. 12.1.5 I_{CCH} Test Circuit

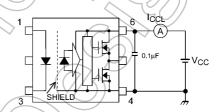
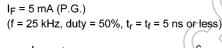
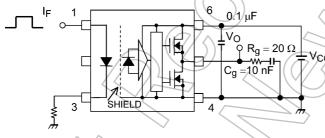
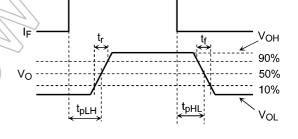


Fig. 12.1.6 I_{CCL} Test Circuit







P.G.: Pulse Generator

Fig. 12.1.7 Switching Time Test Circuit and Waveform

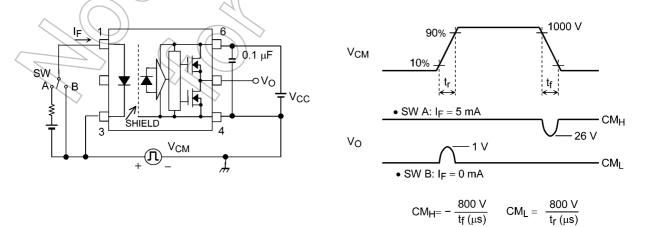
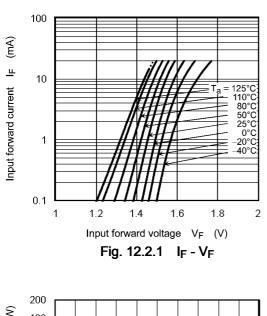
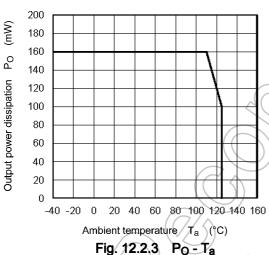


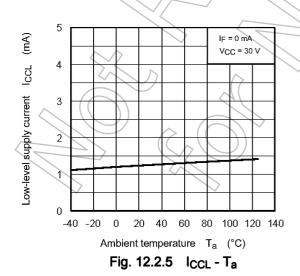
Fig. 12.1.8 Common-Mode Transient Immunity and Waveform

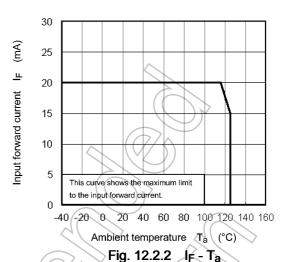


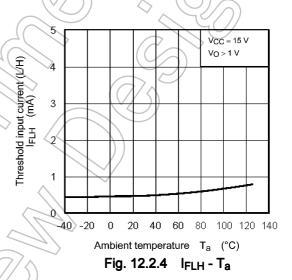
12.2. Characteristics Curves (Note)

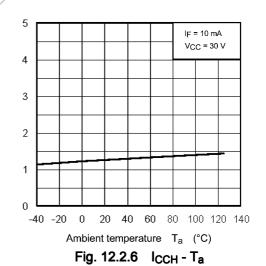










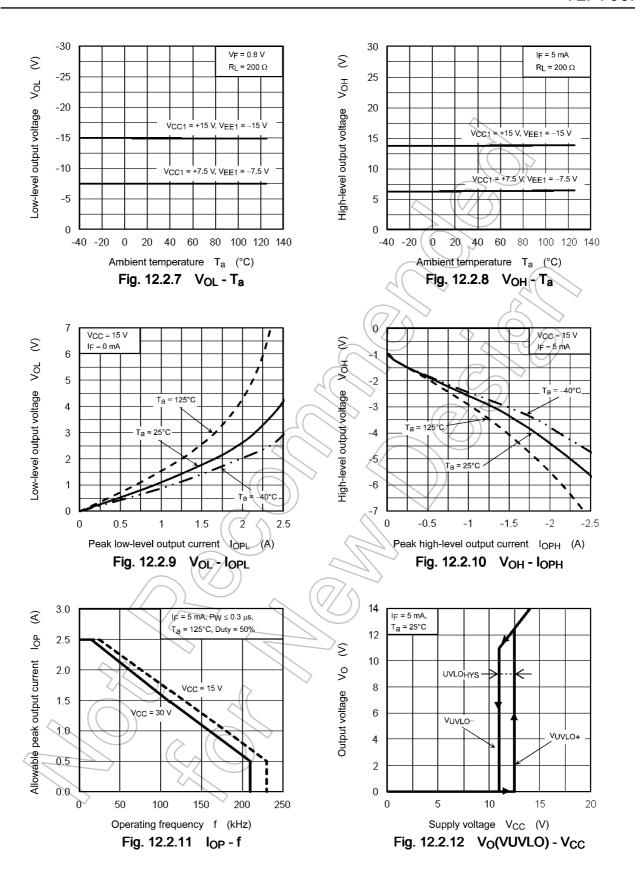


Rev.7.0

I_{CCH}

High-level supply current







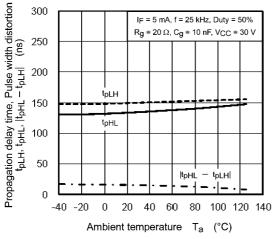


Fig. 12.2.13 t_{pLH} , t_{pHL} , $|t_{pHL}-t_{pLH}|$ - T_a

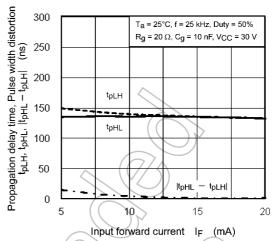


Fig. 12.2.14 tpLH, tpHL, |tpHL-tpLH| - IF

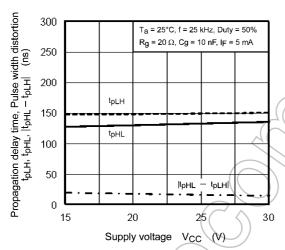


Fig. 12.2.15 t_{pLH}, t_{pHL}, |t_{pHL}-t_{pLH}| - V_{CC}

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.





13. Soldering and Storage

13.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

· When using soldering reflow.

The soldering temperature profile is based on the package surface temperature. (See the figure shown below, which is based on the package surface temperature.)

Reflow soldering must be performed once or twice.

The mounting should be completed with the interval from the first to the last mountings being 2 weeks.

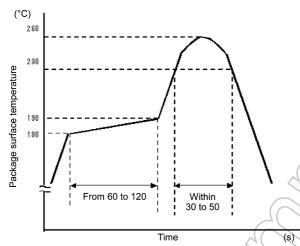


Fig. 13.1.1 An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

When using soldering flow

Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds.

Mounting condition of 260 °C within 10 seconds is recommended.

Flow soldering must be performed once.

· When using soldering Iron

Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C

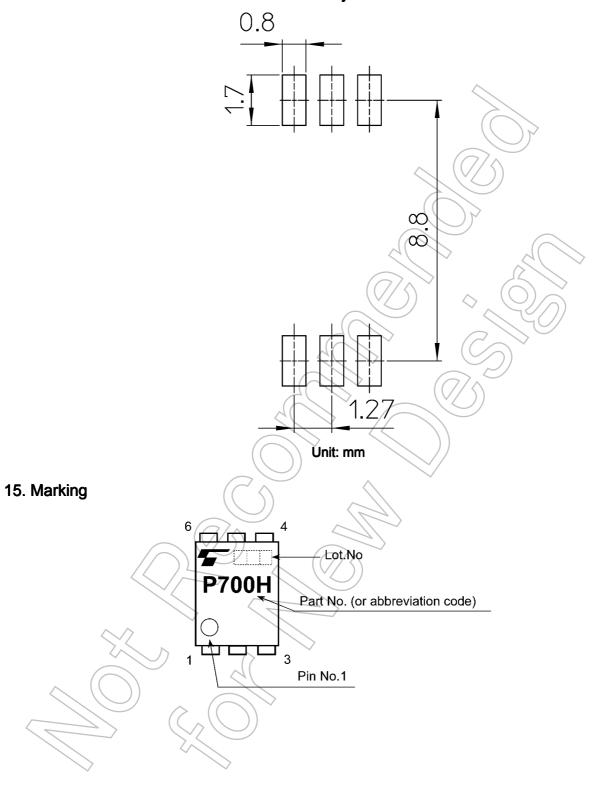
Heating by soldering iron must be done only once per lead.

13.2. Precautions for General Storage

- · Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- · When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.



14. Land Pattern Dimensions for Reference Only





16. EN 60747-5-5 Option (D4) Specification

- Part number: TLP700H, TLP700HF (Note 1)
- The following part naming conventions are used for the devices that have been qualified according to option (D4) of EN 60747.

Example: TLP700H(D4-TP, F)

D4: EN 60747 option

TP: Tape type

F: [[G]]/RoHS COMPATIBLE (Note 2)

Note 1: Use TOSHIBA standard type number for safety standard application: e.g., TLP700H(D4-TP, F) → TLP700H

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronics equipment.

Description		Symbol	Rating	Unit	
Application classification					
for rated mains voltage ≤ 300 Vrms for rated mains voltage ≤ 600 Vrms		775	I-IV I-III	_	
Climatic classification			40 / 125 / 21	_	
Pollution degree			2	_	
	TLPxxx type	.,	890) (a 1	
Maximum operating insulation voltage	TLPxxxF type	VIORM	1140	Vpeak	
Input to output test voltage, Method A	TLPxxx type	.,	1424		
V_{pr} = 1.6 × V_{IORM} , type and sample test t_p = 10 s, partial discharge < 5 pC	TLPxxxF type	- V _{pr}	1824	Vpeak	
Input to output test voltage, Method B	TLPxxx type		1670) (n = =	
V _{pr} = 1.875 × V _{IORM} , 100 % production test t _p = 1 s, partial discharge < 5 pC	TLPxxxF type	V _{pr}	2140	Vpeak	
Highest permissible overvoltage (transient overvoltage, t _{pr} = 60 s)	VTR	8000	Vpeak		
Safety limiting values (max. permissible ratings in case of also refer to thermal derating current (input current $ F, P_{SO} = 0$) power (output or total power dissipation) temperature		I _{si} P _{so} T _s	300 700 150	mA mW °C	
Insulation resistance V_{IO} = 500 V, T_a = 25 °C V_{IO} = 500 V, T_a = 100 °C V_{IO} = 500 V, T_a = T_s	R _{si}	≥ 10 ¹² ≥ 10 ¹¹ ≥ 10 ⁹	Ω		

Fig. 16.1 EN 60747 Isolation Characteristics



		7.62-mm pitch TLPxxx type	10.16-mm pitch TLPxxxF type	
Minimum creepage distance	Cr	7.0 mm	8.0 mm	
Minimum clearance	CI	7.0 mm	8.0 mm	
Minimum insulation thickness	ti	0.4 mm		
Comparative tracking index	СТІ	175		

Fig. 16.2 Insulation Related Specifications (Note)

Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.

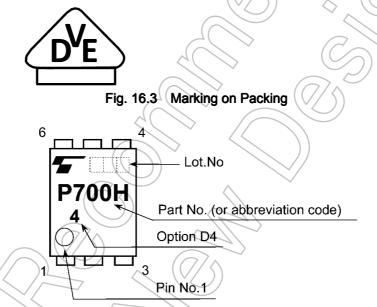
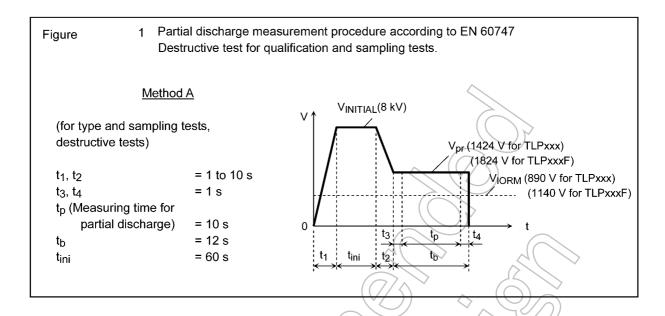
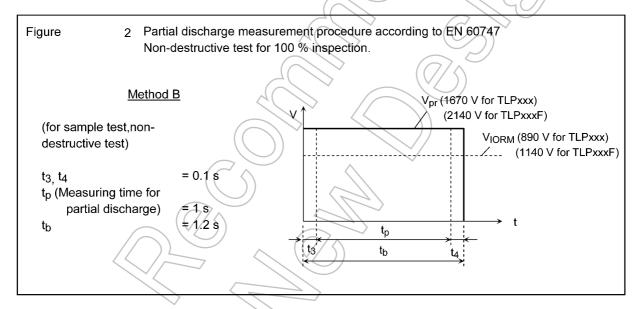


Fig. 16.4 Marking Example (Note)

Note: The above marking is applied to the photocouplers that have been qualified according to option (D4) of EN 60747.







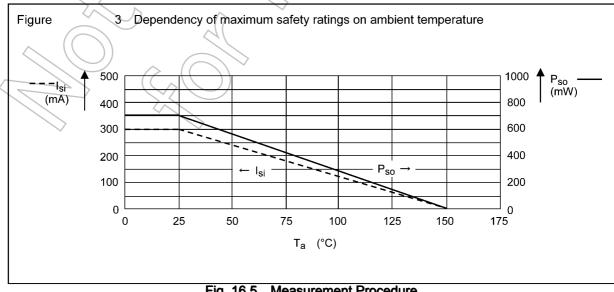
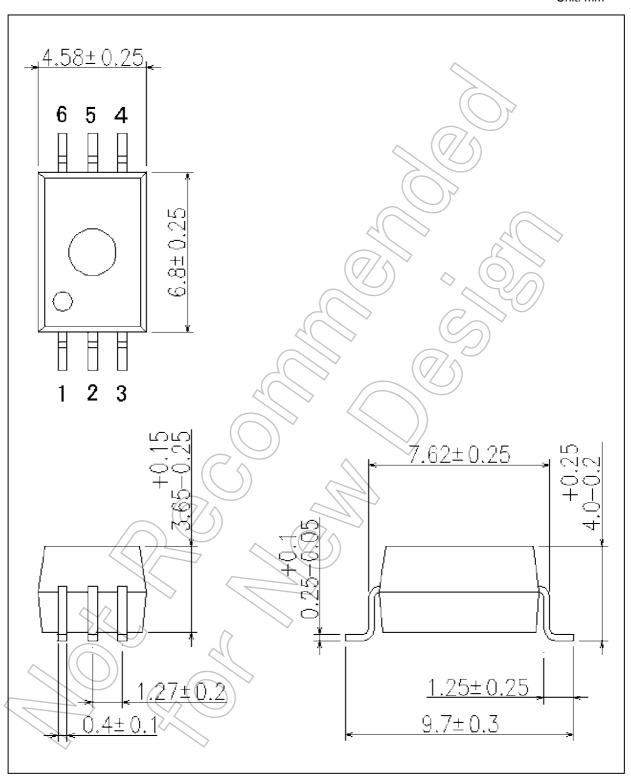


Fig. 16.5 Measurement Procedure



Package Dimensions

Unit: mm



Weight: 0.26 g (typ.)

	Package Name(s)
TOSHIBA: 11-5J1S	



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